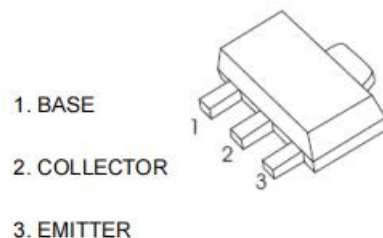


SOT-89-3L Bipolar Transistor 双极型三极管

■ Features 特点

PNP High Speed Switching 高速开关
Low Saturation Voltage 低饱和压降



■ Absolute Maximum Ratings 最大额定值

| Characteristic 特性参数 | Symbol 符号 | Rat 额定值 | Unit 单位 |
|---------------------------------------------|-----------------------------|----------------------------|---------------------------|
| Collector-Base Voltage 集电极基极电压 | V_{CBO} | -50 | V |
| Collector-Emitter Voltage 集电极发射极电压 | V_{CEO} | -50 | V |
| Emitter-Base Voltage 发射极基极电压 | V_{EBO} | -5 | V |
| Collector Current 集电极电流 | I_C | -2000 | mA |
| Power dissipation 耗散功率 | $P_C(T_a=25^\circ\text{C})$ | 500 | mW |
| Thermal Resistance Junction-Ambient 热阻 | $R_{\theta JA}$ | 250 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature 结温和储藏温度 | T_J, T_{stg} | -55to+150 $^\circ\text{C}$ | |

■ Device Marking 产品打标

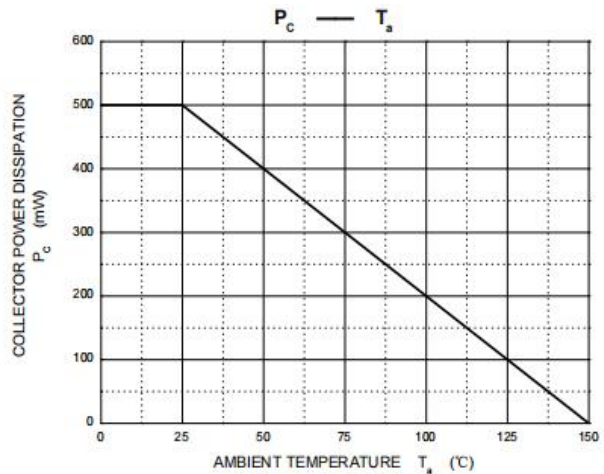
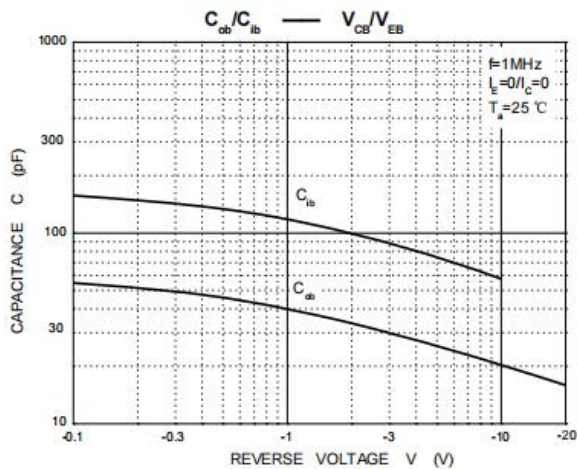
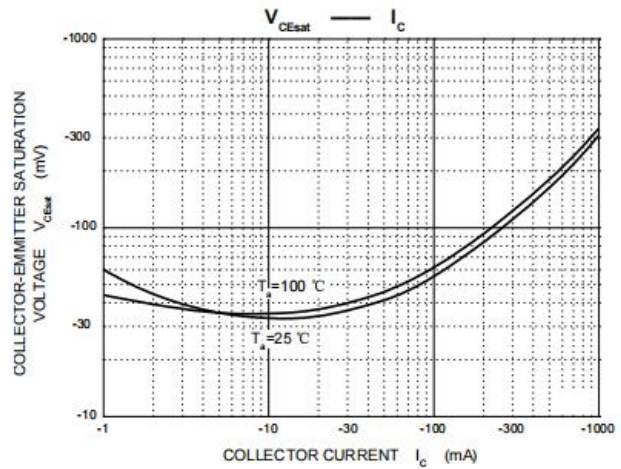
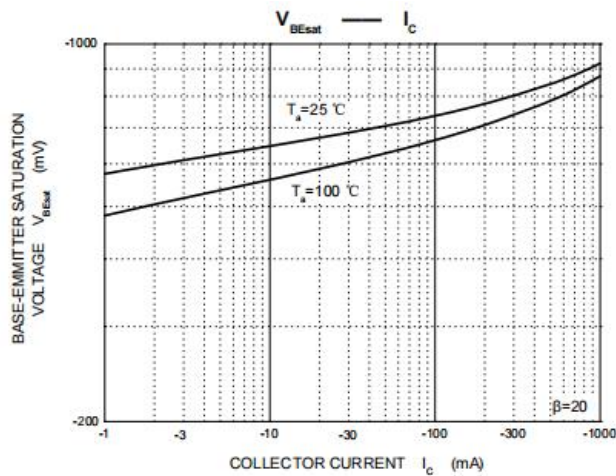
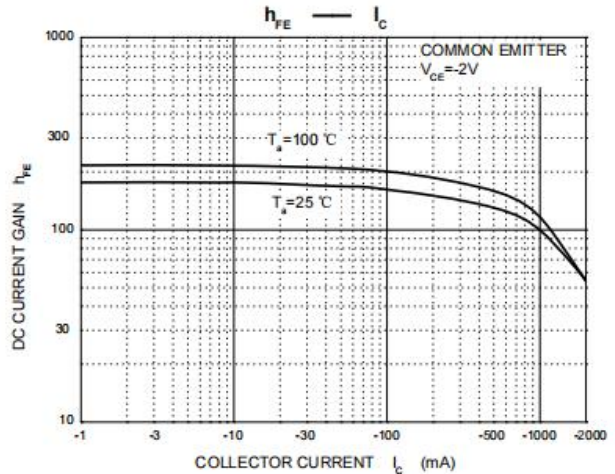
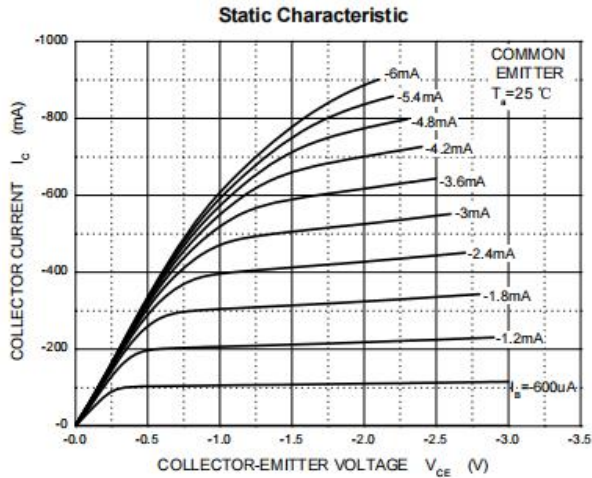
| | | |
|----------|-----------|------------|
| H_{FE} | 70-140(O) | 120-240(Y) |
| Mark | NO | NY |

■ Electrical Characteristics 电特性

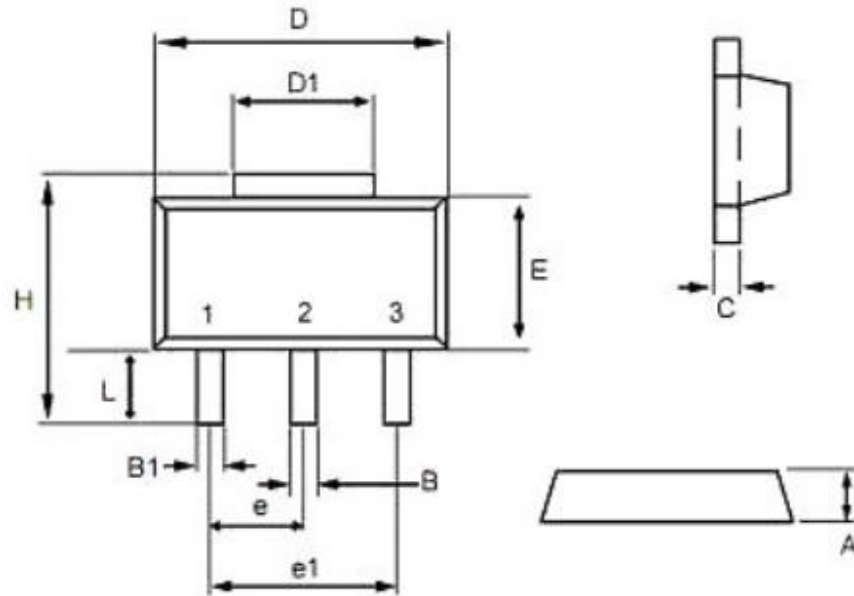
($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

| Characteristic 特性参数 | Symbol 符号 | Min 最小值 | Type 典型值 | Max 最大值 | Unit 单位 |
|------------------------------------------------------------------------------------------------------------------------------|---------------|------------|-------------|------------|------------|
| Collector-Base Breakdown Voltage 集电极基极击穿电压($I_C = -100\mu\text{A}$, $I_E = 0$) | BV_{CBO} | -50 | — | — | V |
| Collector-Emitter Breakdown Voltage 集电极发射极击穿电压($I_C = -1\text{mA}$, $I_B = 0$) | BV_{CEO} | -50 | — | — | V |
| Emitter-Base Breakdown Voltage 发射极基极击穿电压($I_E = -100\mu\text{A}$, $I_C = 0$) | BV_{EBO} | -5 | — | — | V |
| Collector-Base Leakage Current 集电极基极漏电流($V_{CB} = -50\text{V}$, $I_E = 0$) | I_{CBO} | — | — | -100 | nA |
| Emitter-Base Leakage Current 发射极基极漏电流($V_{EB} = -5\text{V}$, $I_C = 0$) | I_{EBO} | — | — | -100 | nA |
| DC Current Gain($V_{CE} = -2\text{V}$, $I_C = -500\text{mA}$) 直流电流增益($V_{CE} = -2\text{V}$, $I_C = -2000\text{mA}$) | H_{FE} | 70 20 | — | 240 | |
| Collector-Emitter Saturation Voltage 集电极发射极饱和压降($I_C = -1000\text{mA}$, $I_B = -50\text{mA}$) | $V_{CE(sat)}$ | — | — | -500 | mV |
| Base-Emitter Saturation Voltage 基极发射极饱和压降($I_C = -1000\text{mA}$, $I_B = -50\text{mA}$) | $V_{BE(sat)}$ | — | — | -1200 | mV |
| Turn-on Time 开通时间 ($V_{CC} = -50\text{V}$, $I_C = -700\text{mA}$, $I_{B1} = -I_{B2} = -70\text{mA}$) | t_{on} | — | 80 | — | ns |
| Storage Time 贮存时间 ($V_{CC} = -50\text{V}$, $I_C = -700\text{mA}$, $I_{B1} = -I_{B2} = -70\text{mA}$) | t_s | — | 750 | — | ns |
| Fall Time 下降时间 ($V_{CC} = -50\text{V}$, $I_C = -700\text{mA}$, $I_{B1} = -I_{B2} = -70\text{mA}$) | t_f | — | 40 | — | ns |
| Transition Frequency 特征频率($V_{CE} = -2\text{V}$, $I_C = -500\text{mA}$) | f_T | — | 100 | — | MHz |
| Output Capacitance 输出电容($V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$) | C_{ob} | — | 40 | — | pF |

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 1.40 | 1.60 | 0.055 | 0.063 |
| B | 0.40 | 0.56 | 0.016 | 0.022 |
| B1 | 0.35 | 0.48 | 0.014 | 0.019 |
| C | 0.35 | 0.44 | 0.014 | 0.017 |
| D | 4.40 | 4.60 | 0.173 | 0.181 |
| D1 | 1.35 | 1.83 | 0.053 | 0.072 |
| e | 1.45 | 1.55 | 0.057 | 0.061 |
| e1 | 2.95 | 3.05 | 0.116 | 0.120 |
| E | 2.29 | 2.60 | 0.090 | 0.102 |
| H | 3.75 | 4.25 | 0.148 | 0.167 |
| L | 0.80 | 1.20 | 0.031 | 0.047 |